SemTron Microtech Corporation

SMC4802M

Dual N-Channel MOSFET

■DESCRIPTION

SMC4802 is the Dual N-Channel enhancement mode power field effect transistors are using trench DMOS technology.This advanced technology has been especially tailored to minimize on-state resistance.This device is ideal for load switch applications.

■PART NUMBER INFORMATION

SMC 4802 M - TR G
a b c d e

a : Company name.
b : Product Serial number.
c : Package code M:SOP-8
d : Handling code TR:Tape&Reel
e : Green produce code G:*RoHS Compliant*

■FEATURES

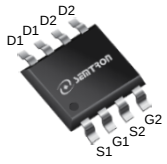
V_{DS} = 30V, I_D = 12A

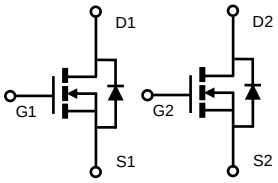
$R_{DS(ON)}$=7mΩ(Typ.)@V_{GS}=10V
$R_{DS(ON)}$=8mΩ(Typ.)@V_{GS}=4.5V

◆100% EAS Guaranteed
◆Improved dv/dt capability
◆High power and current handling capability

■APPLICATIONS

◆Power Management
◆DC/DC Power System
◆Load Switch





SOP-8

■ABSOLUTE MAXIMUM RATINGS (T_A = 25°C Unless otherwise noted)

Symbol	Parameter		Rating	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A=25°C	12	A
		T_A=70°C	9.5	A
I_{DM}	Pulsed Drain Current [A]		48	A
I_{AS}	Avalanche Current [A]		30	A
E_{AS}	Single Pulse Avalanche energy L=0.1mH [AE]		45	mJ
P_D	Power Dissipation [B]	T_A=25°C	1.9	W
		T_A=70°C	1.2	W
T_J	Operation Junction Temperature		-55/150	°C
T_{STG}	Storage Temperature Range		-55/150	°C

■THERMAL RESISTANCE

Symbol	Parameter		Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient [B]	t≦10s		65	°C/W
	Thermal Resistance Junction to Ambient [BC]	Steady-State		90	
$R_{\theta JC}$	Thermal Resistance Junction to Case			38	

■ELECTRICAL CHARACTERISTICS(T_A = 25°C Unless otherwise noted)

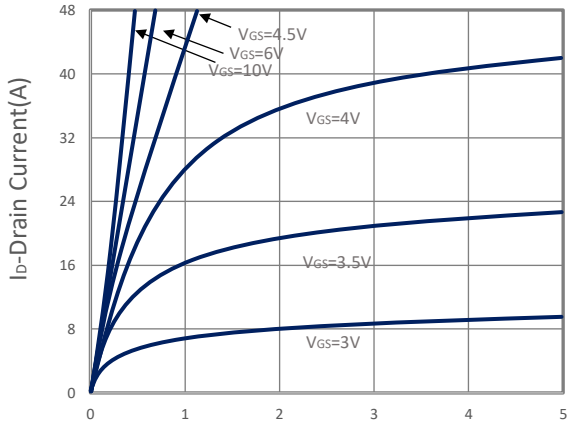
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1	1.6	2.5	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V, T_J=25°C			1	μA
		V_{DS}=24V, V_{GS}=0V, T_J=75°C			10	
$R_{DS(ON)}$	Drain-source On-Resistance [E]	V_{GS}=10V, I_D=12A		7	8.5	mΩ
		V_{GS}=4.5V, I_D=10A		8	11	
G_{fs}	Forward Transconductance	V_{DS}=10V, I_D=10A		8.8		S
Diode Characteristics						
V_{SD}	Diode Forward Voltage [E]	I_S=1A, V_{GS}=0V			1	V
I_S	Continuous Source Current				12	A
t_{rr}	Revese Recovery Time	I_S=10A, dI/dt=100A/μs		12		ns
Q_{rr}	Reverse Recovery Charge			3.5		nC
Dynamic and Switching Parameters						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_D=10A		24.6	33.4	nC
Q_g	Total Gate Charge (4.5V)			12	15	
Q_{gs}	Gate-Source Charge			2.8	3.5	
Q_{gd}	Gate-Drain Charge			6	8.1	
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz		1280		pF
C_{oss}	Output Capacitance			196		
C_{rss}	Reverse Transfer Capacitance			162		
R_g	Gate Resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz		2.2		
$t_{d(on)}$	Turn-On Time	V_{DD}=15V, V_{GEN}=10V R_G=3.3Ω, I_D=1A		6.4	12	nS
t_r				14	27	
$t_{d(off)}$	Turn-Off Time			32.4	62	
t_f				9.2	17	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

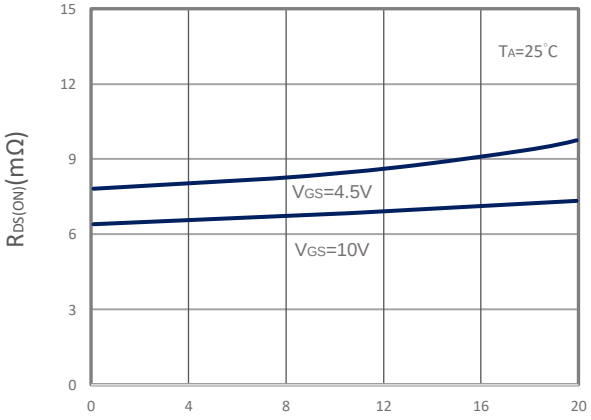
A. Pulsed width limited by maximum junction temperature, $T_{J(MAX)}$=150°C.
B. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board in a still air environment with maximum junction temperature $T_{J(MAX)}$=150°C (initial temperature T_A=25°C).
C. $T_{J(MAX)}$=150°C,using junction-to-case thermal resistance ($R_{\theta JC}$) is more useful in additional heat sinking is used.
D. The data tested by pulsed , pulse width ≦ 300μS , duty cycle ≦ 2%.
E. The E_{AS} data shows Max, tested and pulse width limited by $T_{J(MAX)}$=150°C (initial temperature T_J=25°C).

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this datasheet.

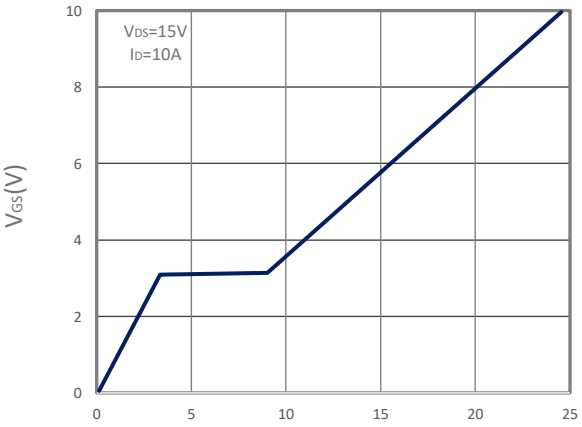
TYPICAL CHARACTERISTICS



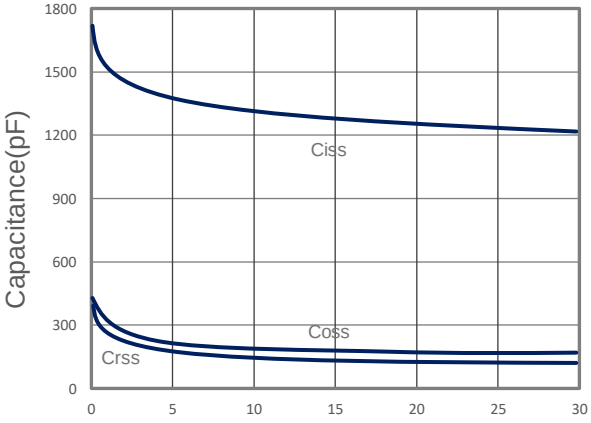
Output Characteristics



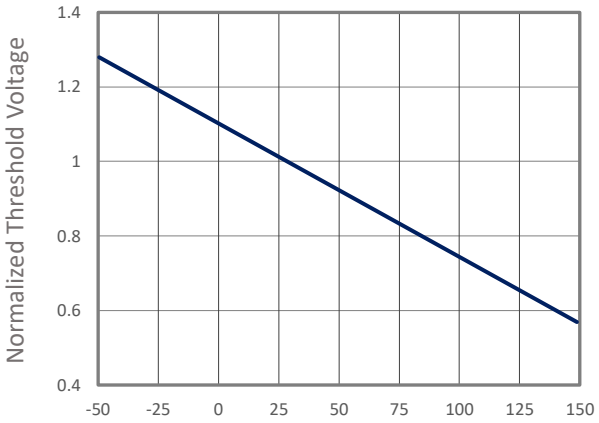
Drain-Source On Resistance



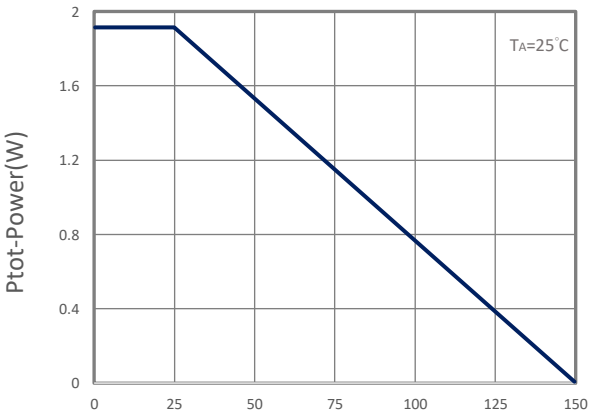
Gate Charge



Capacitance

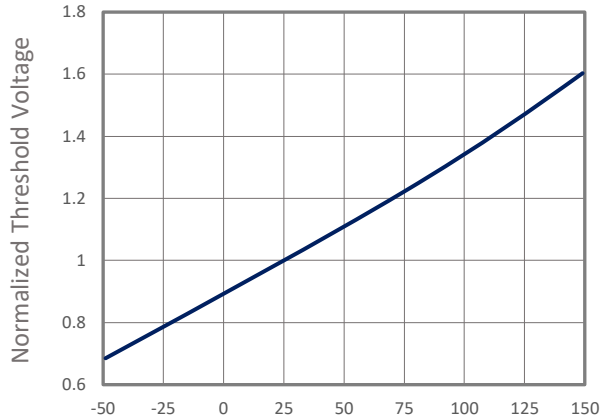


Gate Threshold Voltage

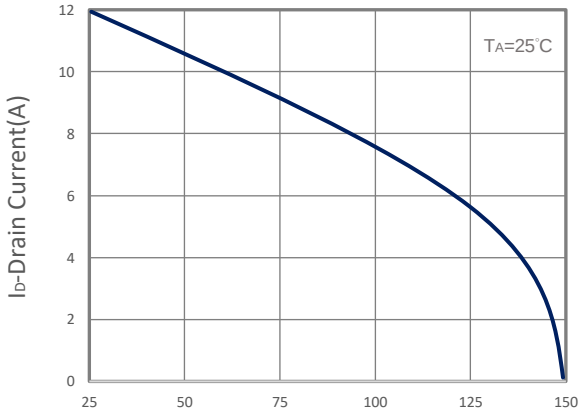


Power Dissipation

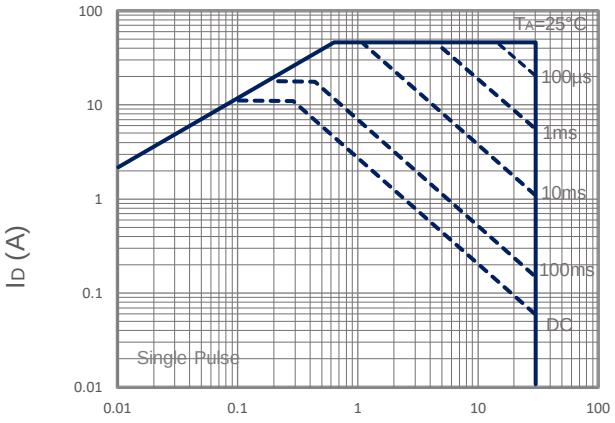
TYPICAL CHARACTERISTICS



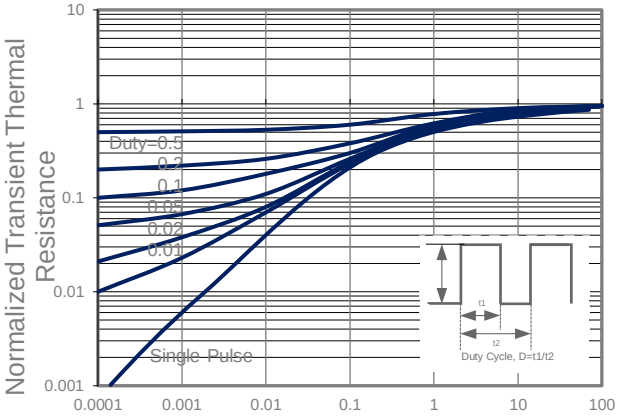
Gate Threshold Voltage



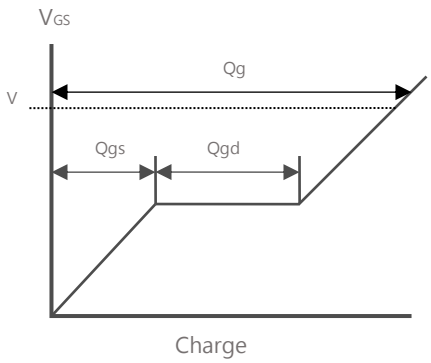
Drain Current vs TJ



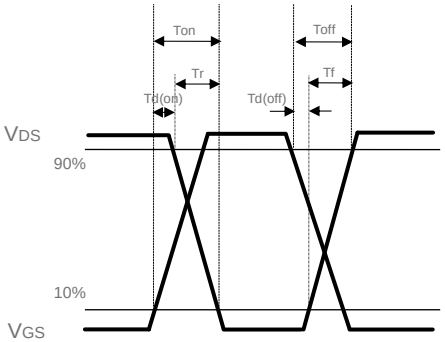
Maximum Safe Operation Area



Thermal Transient Impedance

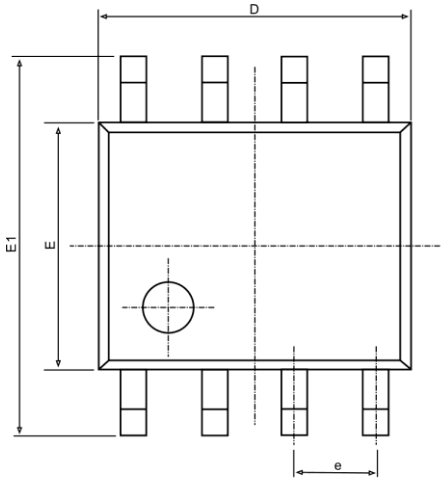


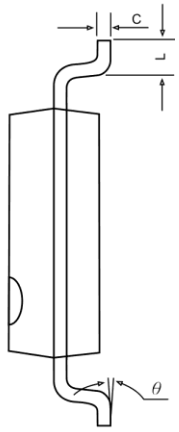
Gate Chrge Waveform

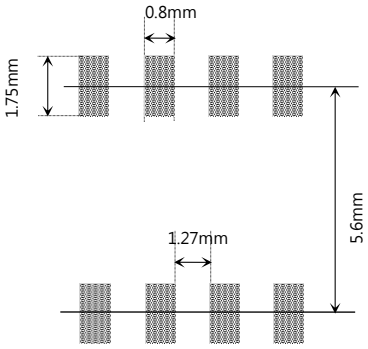


Switching Time Waveform

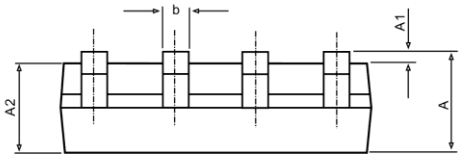
■SOP-8 PACKAGE DIMENSIONS







Recommended Land Pattern



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.040.	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.130	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270BSC.		0.050BSC.	
L	0.400	1.270	0.016	0.005
Θ	0°	8°	0°	8°